

DMTH4M75SPSW

40V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

BV _{DSS}	Rds(on) Max	I _D Max Tc = +25°C
40V	$0.75 m\Omega @ V_{GS} = 10V$	337A

Description and Applications

This new generation MOSFET is designed to minimize R_{DS(ON)} yet maintain superior switching performance. This device is ideal for use in power management and load switches.

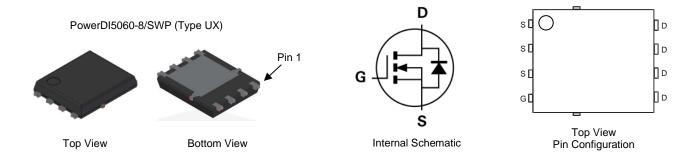
- Engine-management systems
- Body control electronics
- DC-DC converters

Features and Benefits

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- Thermally Efficient Package-Cooler Running Applications
- High Conversion Efficiency
- Wettable Flank for Improved Optical Inspection
- Low RDS(ON) Minimizes On-State Losses
- < 1.1mm Package Profile Ideal for Thin Applications</p>
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. <u>https://www.diodes.com/quality/product-definitions/</u>

Mechanical Data

- Package: PowerDI[®]5060-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (63)
- Weight: 0.097 grams (Approximate)



Ordering Information (Note 4)

Orderable Part Number	Backago	Packing		
Orderable Fait Nulliber	Package	Qty.	Carrier	
DMTH4M75SPSW-13	PowerDI5060-8/SWP (Type UX)	2500	Tape & Reel	

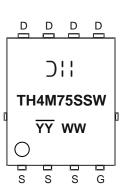
Notes: 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and

Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information



PowerDI5060-8/SWP (Type UX)

 D_{II} = Manufacturer's Marking TH4M75SSW = Product Type Marking Code YYWW or \overline{YY} = Date Code Marking YY or \overline{YY} = Last Two Digits of Year (ex: 24 = 2024) WW = Week Code (01 to 53)

Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	40	V	
Gate-Source Voltage		Vgss	±20	V
Continuous Drain Current, V _{GS} = 10V (Note 5)	Tc = +25°C T _C = +100°C	ID	337 238	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		IDM	1348	А
Continuous Body Diode Forward Current (Note 5)	Tc = +25°C	ls	337	А
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)	lsм	1348	А	
Avalanche Current, L = 1mH		las	40	А
Avalanche Energy, L = 1mH		Eas	800	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)	T _A = +25°C	PD	3.9	W
Thermal Resistance, Junction to Ambient (Note 6)		Reja	38	°C/W
Total Power Dissipation (Note 5)	$T_{\rm C} = +25^{\circ}{\rm C}$	PD	150	W
Thermal Resistance, Junction to Case (Note 5)	·	Rejc	1.0	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +175	°C

Notes:

Thermal resistance from junction to soldering point (on the exposed drain pad).
 Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

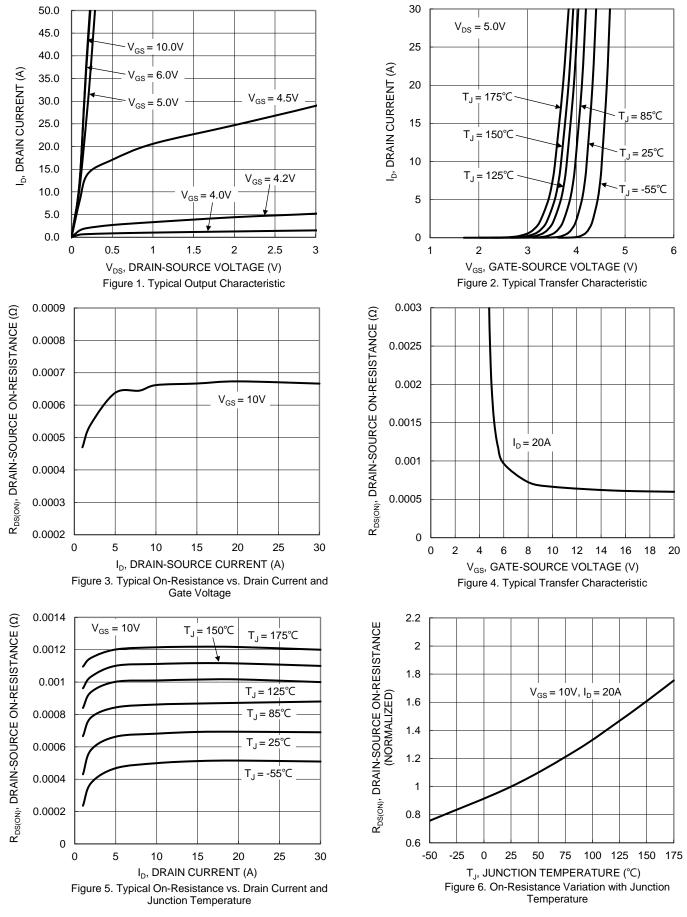
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BVDSS	40			V	V _{GS} = 0, I _D = 1mA	
Zero Gate Voltage Drain Current	IDSS	_		1	μA	V _{DS} = 32V, V _{GS} = 0	
Gate-Source Leakage	Igss	_	—	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	VGS(TH)	2	—	4	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	0.5	0.75	mΩ	$V_{GS} = 10V, I_D = 20A$	
Diode Forward Voltage	V _{SD}	_	0.8	1.3	V	$V_{GS} = 0, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	_	9434	_	pF	$V_{DS} = 20V, V_{GS} = 0$ f = 1MHz	
Output Capacitance	Coss	_	4466	_			
Reverse Transfer Capacitance	Crss	_	271	_			
Gate Resistance	Rg	_	2.3	_	Ω	$V_{DS} = 0$, $V_{GS} = 0$, $f = 1MHz$	
Total Gate Charge	Qg	_	115	_		V _{DD} = 20V, I _D = 20A, V _{GS} = 10V	
Gate-Source Charge	Q _{gs}	_	29	_	nC		
Gate-Drain Charge	Q _{gd}	—	5	_			
Turn-On Delay Time	td(on)	—	16	_		$V_{DD} = 20V, V_{GS} = 10V$ $I_D = 20A, R_g = 2.5\Omega$	
Turn-On Rise Time	t _R	—	37	—			
Turn-Off Delay Time	tD(OFF)	_	82	_	ns		
Turn-Off Fall Time	tF	_	41	_			
Reverse-Recovery Time	trr	—	129	_	ns	I= - 204 di/dt - 1004/up	
Reverse-Recovery Charge	Q _{RR}	_	391		nC	I _F = 20A, di/dt = 100A/μs	

 Notes:
 7. Short duration pulse test used to minimize self-heating effect.

 8. Guaranteed by design. Not subject to product testing.



DMTH4M75SPSW



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 $I_D = 1 m A$

100 125 150 175

Ciss

C

 $C_{\rm rss}$

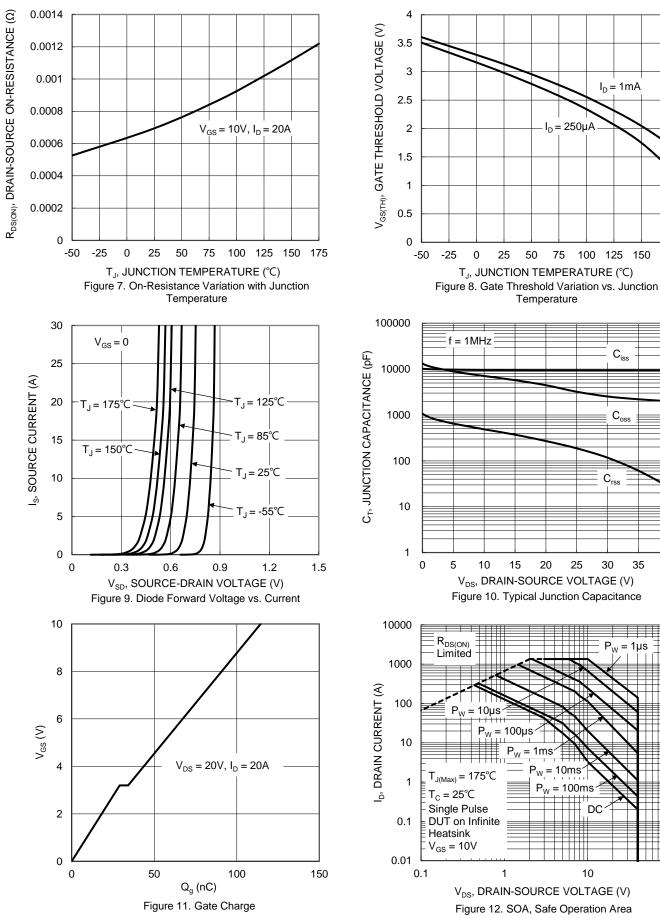
30

35

40

100

25



September 2024

0ms

100ms

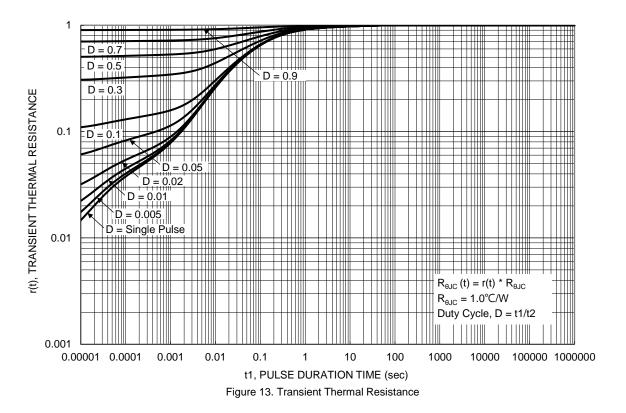
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DMTH4M75SPSW Document number: DS46575 Rev. 3 - 2

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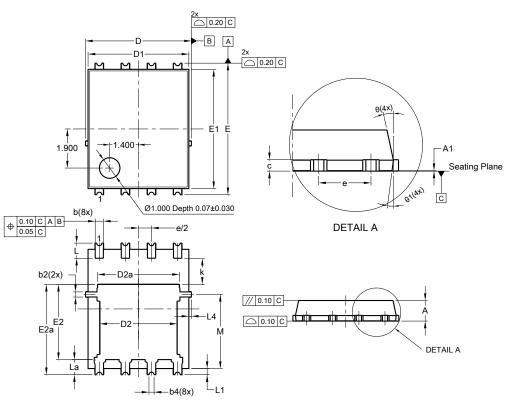


PowerDI5060-8/SWP

(Type UX)

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.



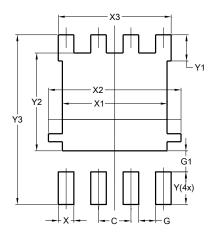
PowerDI5060-8/SWP (Type UX)

Dim Min Max Тур 0.90 1.10 1.00 Α A1 0 0.05 --b 0.30 0.50 0.41 b2 0.20 0.35 0.25 b4 0.25RE 0.230 0.330 0.277 С D 5.15 BSC D1 4.70 5.10 4.90 D2 3.56 3.96 3.76 D2a 3.78 4.18 3.98 Ε 6.40 BS 5.80 E1 5.60 6.00 E2 3.46 3.86 3.66 E2a 4.195 4.595 4.395 е 1.27BSC k 1.05 ------L 0.635 0.835 0.735 La 0.635 0.835 0.735 L1 0.200 0.400 0.300 L4 0.025 0.225 0.125 М 3.205 4.005 3.605 θ <u>11°</u> 10° 12° θ1 6° 8° 7° All Dimensions in mm

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8/SWP (Type UX)



Dimensions	Value (in mm)		
С	1.270		
G	0.660		
G1	0.820		
Х	0.610		
X1	4.100		
X2	5.190		
X3	4.420		
Y	1.270		
Y1	1.020		
Y2	3.810		
Y3	6.610		



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